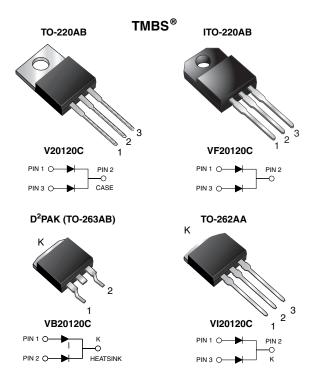
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Dual High Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.54 \text{ V}$ at $I_F = 5 \text{ A}$



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 10 A				
V _{RRM}	120 V				
I _{FSM}	120 A				
V _F at I _F = 10 A	0.64 V				
T _J max.	150 °C				
Package	TO-220AB, ITO-220AB, D ² PAK (TO-263AB), TO-262AA				
Circuit configuration	Common cathode				

FEATURES

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses
- High efficiency operation
- · Low thermal resistance

RoHS COMPLIANT

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for D²PAK (TO-263AB) package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, D²PAK (TO-263AB), and TO-262AA

Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102 E3 suffix meets JESD 201 class 1A whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER		SYMBOL	V20120C	VF20120C	VB20120C	VI20120C	UNIT
Maximum repetitive peak reverse voltage			120				
per device			20				^
Maximum average forward rectified current (fig. 1)	per diode	I _{F(AV)}	10				A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I _{FSM}	120			Α	
Non-repetitive avalanche energy at T _J = 25 °C, L = 60 mH per diode			80			mJ	
Peak repetitive reverse current at t_p = 2 μ s, 1 kHz,TJ = 38 °C \pm 2 °C per diode		I _{RRM}	0.5		Α		
Voltage rate of change (rated V _R)		dV/dt	10 000		V/µs		
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min		V _{AC}	1500			V	
Operating junction and storage temperature range			-40 to +150			°C	

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	$I_R = 1.0 \text{ mA}$	T _A = 25 °C	V_{BR}	120 (minimum)	-	V	
Instantaneous forward voltage per diode	I _F = 5 A	- T _A = 25 °C	V _F ⁽¹⁾	0.62	-	V	
	I _F = 10 A			0.81	0.90		
	I _F = 5 A	T _A = 125 °C		0.54	=		
	I _F = 10 A			0.64	0.72		
Reverse current per diode	V _P = 90 V	T _A = 25 °C	I _R ⁽²⁾	8	-	μΑ	
		T _A = 125 °C		6	=	mA	
	V _R = 120 V	T _A = 25 °C	IR (=)	-	700	μΑ	
		T _A = 125 °C		14	45	mA	

Notes

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	V20120C	VF20120C	VB20120C	VI20120C	UNIT	
Typical thermal resistance per diode	$R_{\theta JC}$	2.8	5.0	2.8	2.8	°C/W	

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	V20120C-E3/4W	1.88	4W	50/tube	Tube		
ITO-220AB	VF20120C-E3/4W	1.75	4W	50/tube	Tube		
D ² PAK (TO-263AB)	VB20120C-E3/4W	1.37	4W	50/tube	Tube		
D ² PAK (TO-263AB)	VB20120C-E3/8W	1.37	8W	800/reel	Tape and reel		
TO-262AA	VI20120C-E3/4W	1.45	4W	50/tube	Tube		

RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

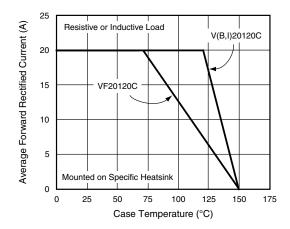


Fig. 1 - Maximum Forward Current Derating Curve

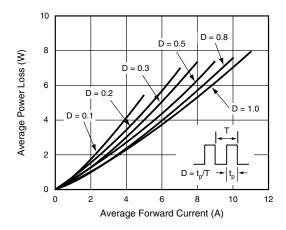


Fig. 2 - Forward Power Loss Characteristics Per Diode

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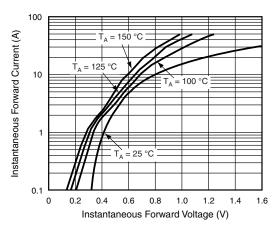


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

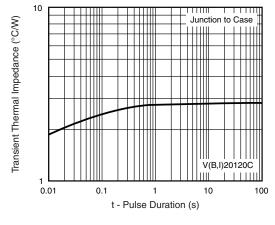


Fig. 6 - Typical Transient Thermal Impedance Per Diode

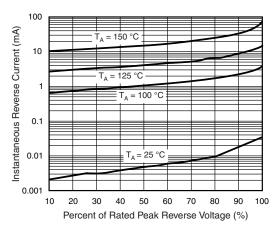


Fig. 4 - Typical Reverse Characteristics Per Diode

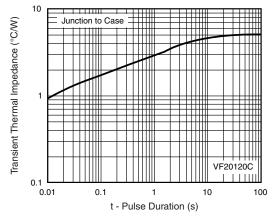


Fig. 7 - Typical Transient Thermal Impedance Per Diode

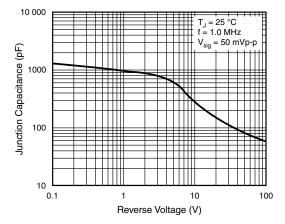
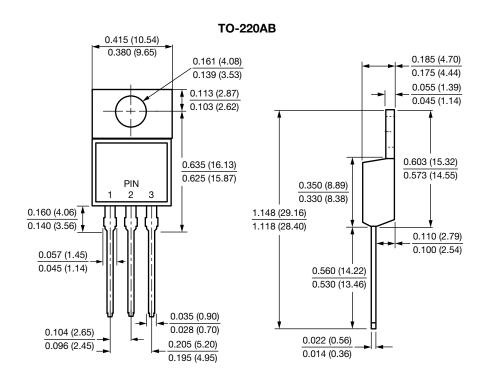


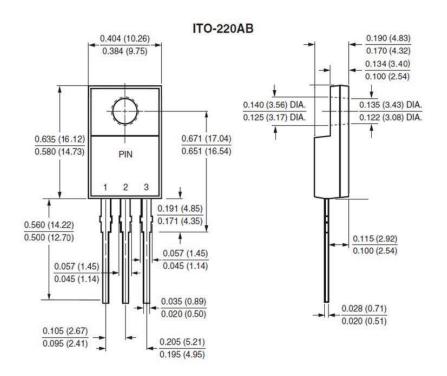
Fig. 5 - Typical Junction Capacitance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

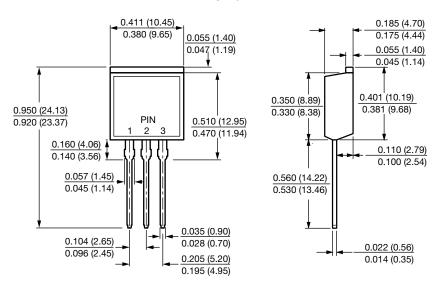




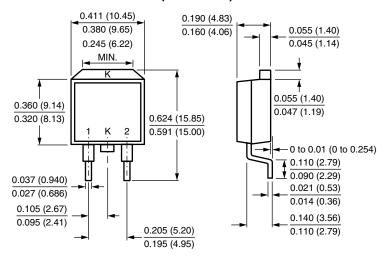
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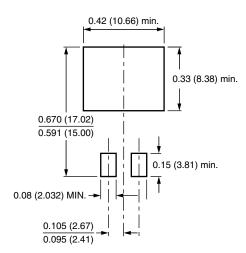
TO-262AA



D²PAK (TO-263AB)



Mounting Pad Layout





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